



YJQ200P10AJ

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-100V
I_D	-8A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	200m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	235m
100% EAS Tested	
100% V_{DS} Tested	

General Description



YJQ200P10AJ

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
-----------	--------	------------	-----	-----	-----	-------

S



YJQ200P10AJ

Typical Electrical 50.57WBT/F5 10.56f1 0 0 1 0.9420.6Tm0 g0 G(2)JT3cfica



YJQ200P10AJ

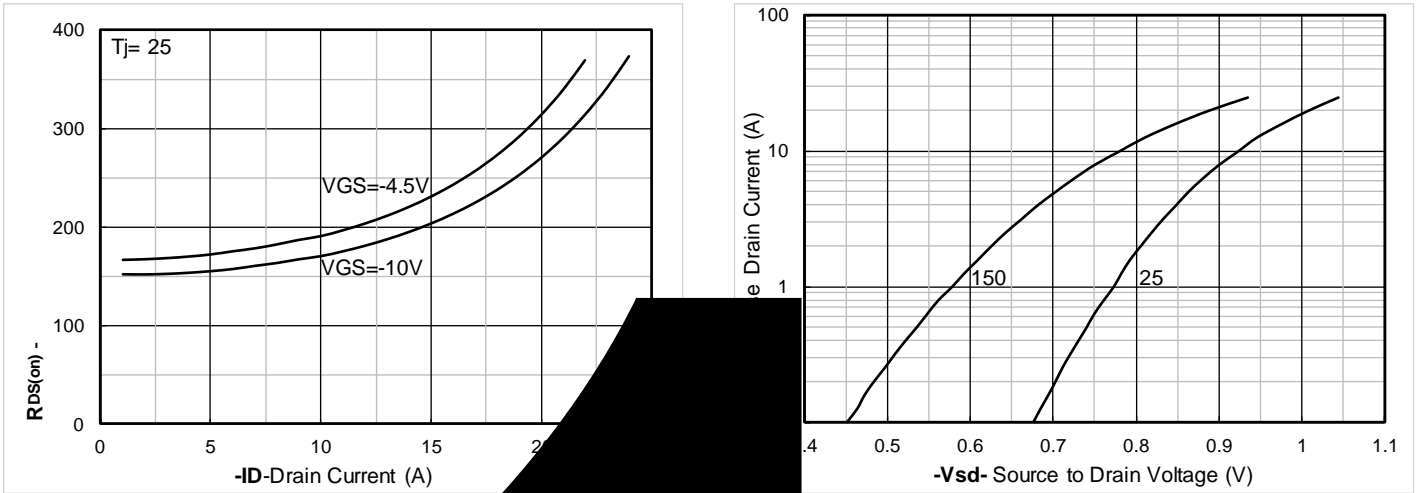


Figure 7. $R_{DS(on)}$ VS Drain Current (A) Figure 8. I_D VS $-V_{SD}$ (V)

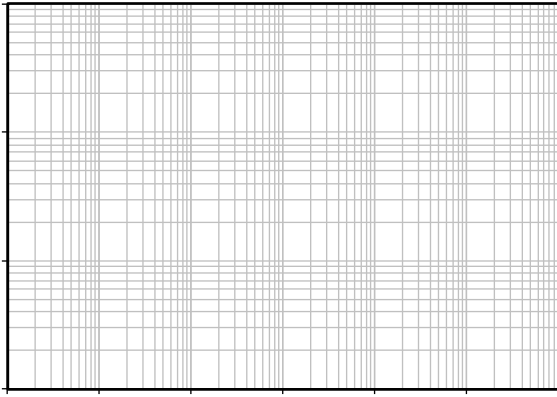


Figure 13. Maximum Transient Thermal Impedance

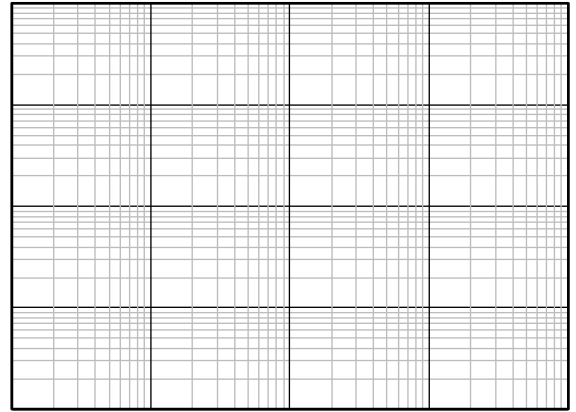
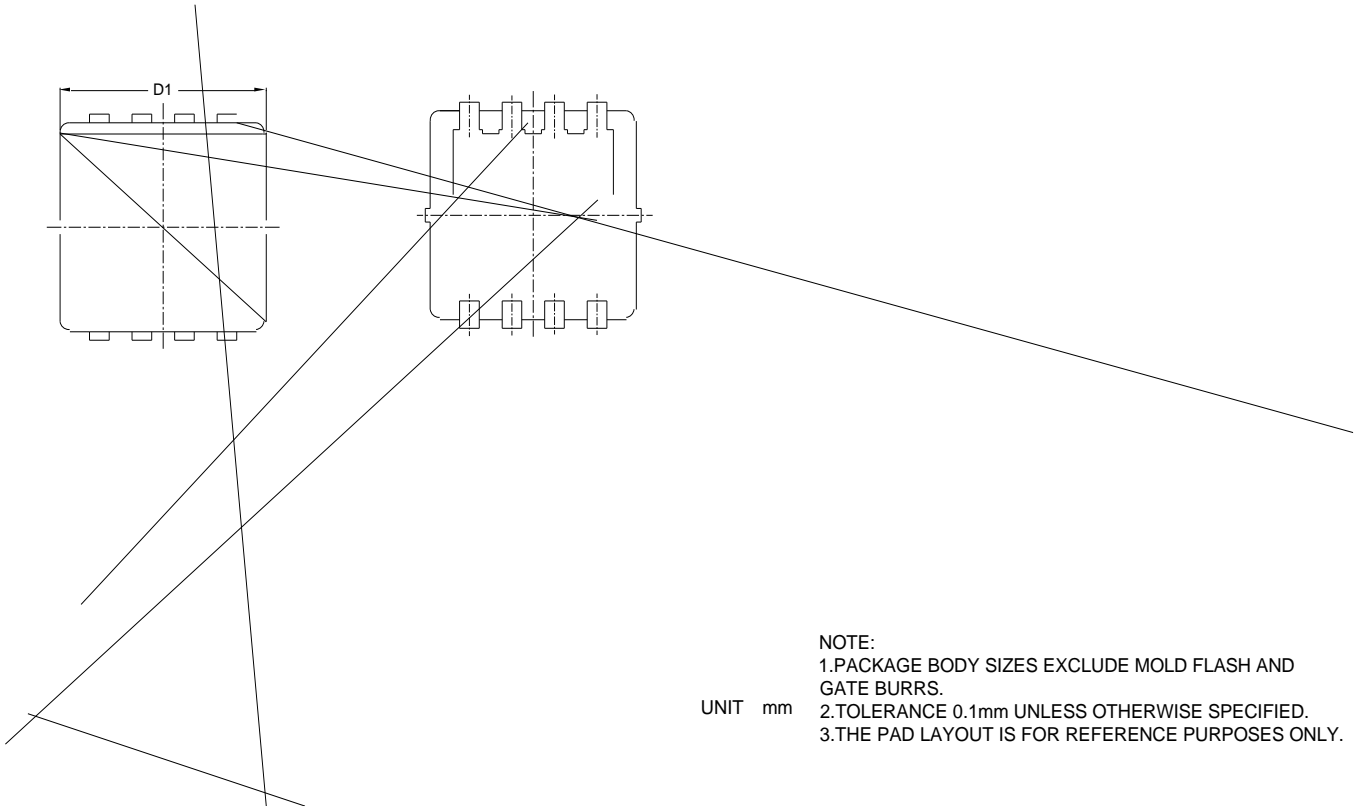


Figure 14. Safe Operation Area



YJQ200P10AJ

PDFN3333-8L-B-0.75MM Package information





YJQ200P10AJ

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the s